

IN THE CLAIMS:

Please amend claims 1-6 as follows:

- Sub B1
Q3
1. (*Once amended*) A vertical cavity surface emitting laser, comprising:
an active region further comprising at least one quantum well having a well depth of at least 40 meV and comprised of InGaAs and further including GaAs barrier layers sandwiching said at least one quantum well; and
GaAs confinement layers sandwiching said active region.
 2. (*Once amended*) The vertical cavity surface emitting laser of claim 1 wherein said at least one quantum well is up to and including 50Å in thickness.
 3. (*Once amended*) A vertical cavity surface emitting laser, comprising:
an active region further comprising at least one quantum well having a well depth of at least 40 meV and comprised of InGaAs and further including GaAsN barrier layers sandwiching said at least one quantum well; and
AlGaAs confinement layers sandwiching said active region.
 4. (*Once amended*) The vertical cavity surface emitting laser of claim 3 wherein said at least one quantum well is up to and including 50Å in thickness.
 5. (*Once amended*) A vertical cavity surface emitting laser, comprising:
an active region further comprising at least one quantum well having a well depth of at least 40 meV and comprised of InGaAs and further including AlGaAs barrier layers sandwiching said at least one quantum well; and
GaAsN confinement layers sandwiching said active region.
 6. (*Once amended*) The vertical cavity surface emitting laser of claim 5 wherein said at least one quantum well is up to and including 50Å in thickness.